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(54) **METHOD FOR PRODUCING A SILICON CARBIDE SEMICONDUCTOR DEVICE**

VERFAHREN ZU HERSTELLUNG EINER SILIZIUMCARBID-HALBLEITERANORDNUNG

PROCÉDÉ DE FABRICATION D'UN DISPOSITIF DE SEMI-CONDUCTEURS EN CARBURE DE SILICIUM

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(56) References cited:
EP-A2- 0 697 716 WO-A-97/17730
US-A1- 2002 153 594

- **TANIMOTO S ET AL: "HIGH-RELIABILITY ONO GATE DIELECTRIC FOR POWER MOSFETS" MATERIALS SCIENCE FORUM, AEDERMANNSDORF, CH, vol. 483-485, 2005, pages 677-680, XP008071439 ISSN: 0255-5476**
- **LIPKIN L ET AL: "CHALLENGES AND STATE-OF-THE-ART OF OXIDES ON SIC" MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS, MATERIALS RESEARCH SOCIETY, PITTSBURG, PA, US, no. 640, 27 November 2000 (2000-11-27), pages H3101-H3110, XP008002243 ISSN: 0272-9172**

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- JAMET PHILIPPE ET AL: "Effects of nitridation in gate oxides grown on 4H-SiC" JOURNAL OF APPLIED PHYSICS, AMERICAN INSTITUTE OF PHYSICS. NEW YORK, US, vol. 90, no. 10, 15 November 2001 (2001-11-15), pages 5058-5063, XP012053541 ISSN: 0021-8979